



Thin Film Photovoltaic Solar Pilot Line

D. L. Morel, C. S. Ferekides, E. K. Stefanakos

Students: R. Anders, K. Jayadevan, B. Satya Kanth, Y. Wang

Department of Electrical Engineering
Clean Energy Research Center
University of South Florida

Collaborators: UF and UCF

Presented at the FESC Review Meeting, Orlando, September, 2010
Department of Electrical Engineering,
Clean Energy Research Center, University of South Florida

Project Overview

Objectives:

Establish a world-class thin film PV module capability

Attract PV manufacturing operations to the state

Project Plan:

Design, build and operate a state-of-the-art generic thin film module facility

Project Overview

Milestones/ Timeline :

Year 1 - Facility operational, sub-module experiments underway

Year 2 – Processing equipment operational, module level processing underway

Year 3 – Demonstration of effective module fabrication and performance, industry participation

Project Overview

Milestones/ Timeline :

*Year 2 – Processing equipment operational,
module level processing underway*

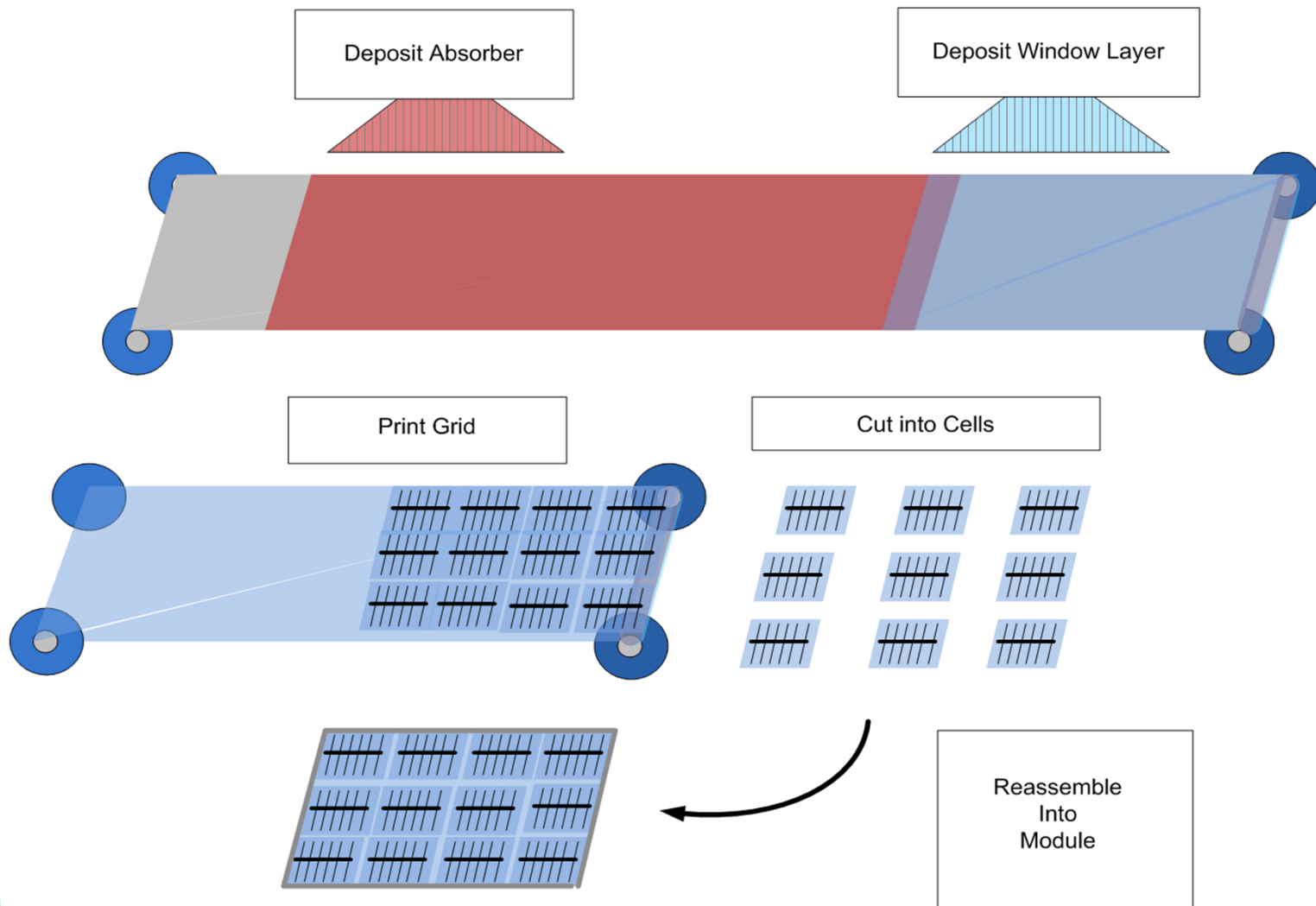
➤ *Formed partnership with Florida based
Mustang Solar*

- *Deposition system budget leveraged by x5*
- *Switched to RTR Processing*
- *SS substrate development underway*

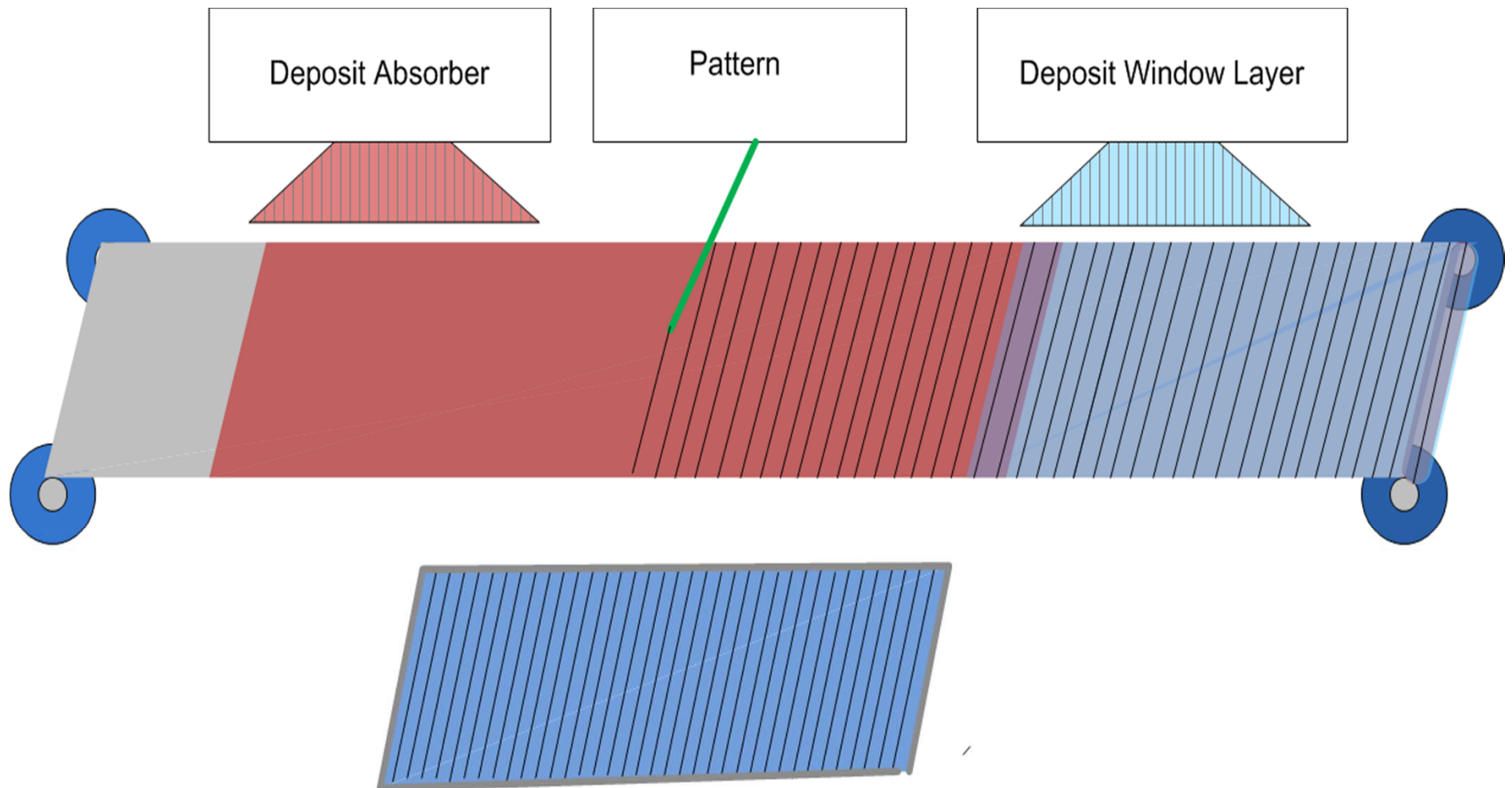
Mustang Solar RTR Coating Machine



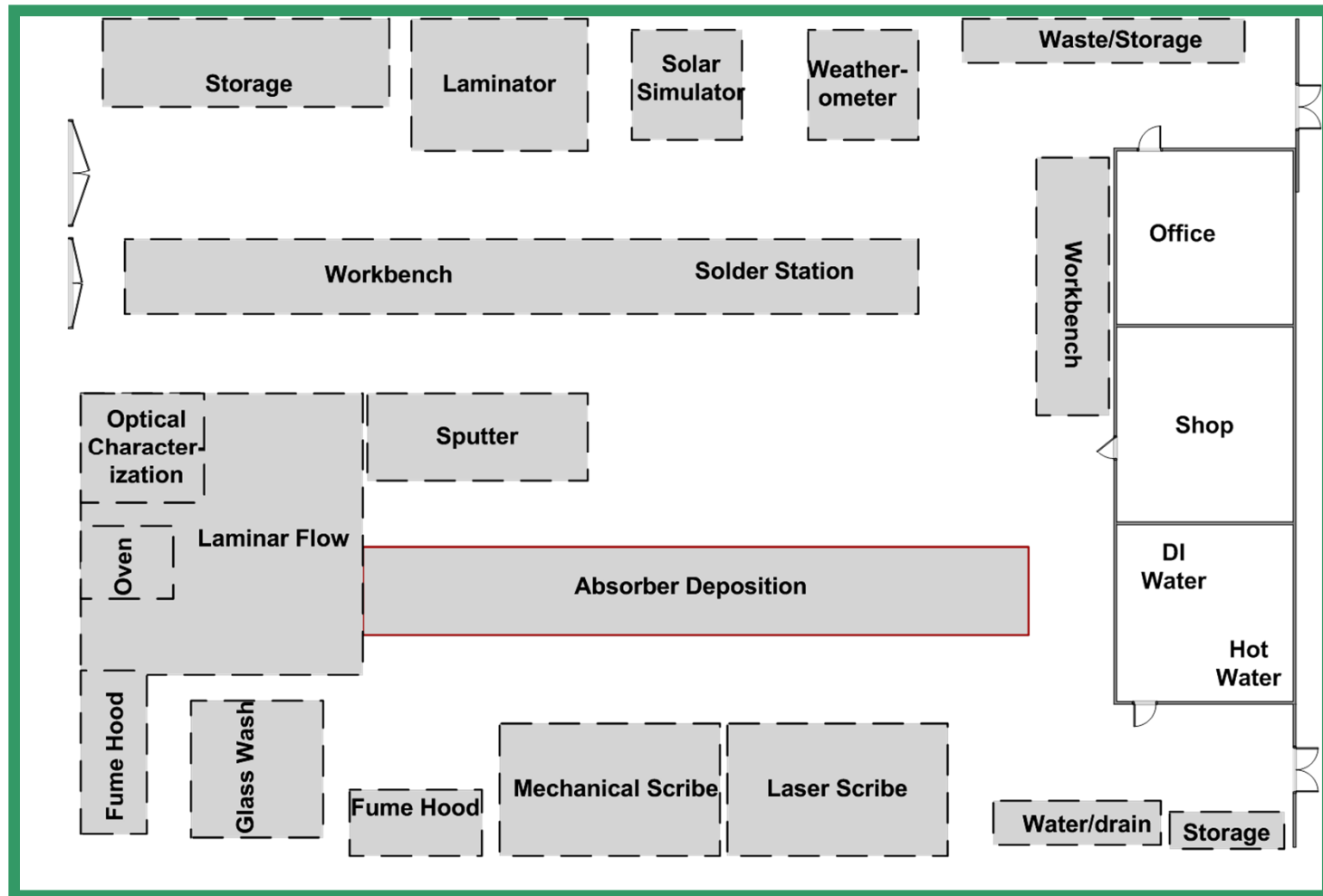
Discrete Cell Production



RTR Monolithic Integrated



Solar PV Laboratory



Solar PV Laboratory

Capabilities

- Cell and Module Fabrication
 - Cell strings on SS roll
 - Interconnection and packaging into modules
 - Monolithic integration in a later phase

- Physical Vapor Deposition
 - Sputtering, Evaporation, Close Space Sublimation

- In-Situ Diagnostics
 - SS integrity, composition and thickness monitoring

- Stability Testing

Selenization Pathways to 2SSS CuInGaSe₂ Manufacturing

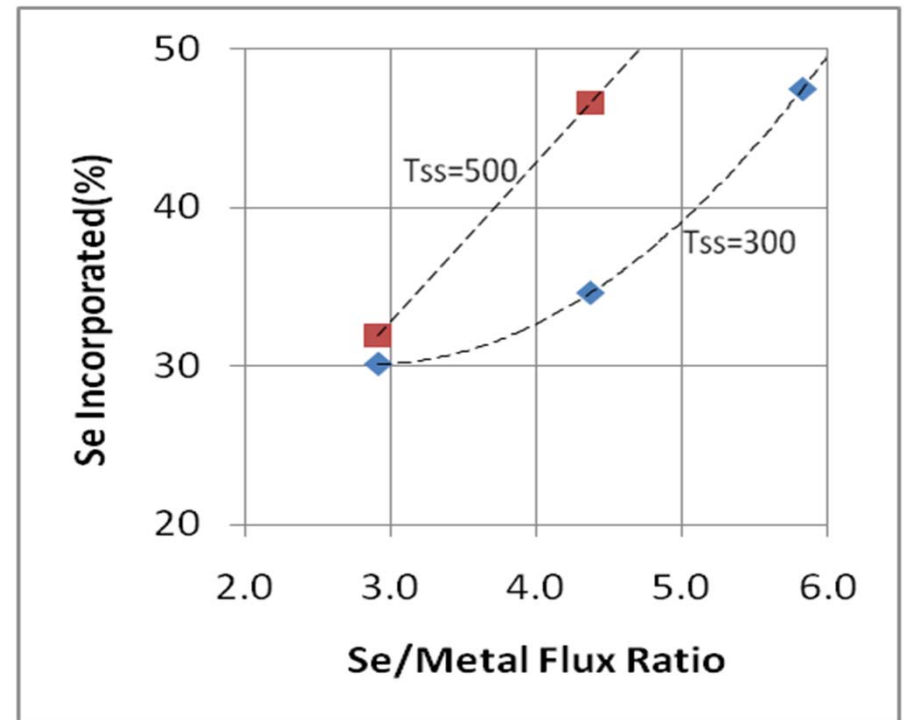
➤ **2SSS : 2 Step Solid Source(Se)**

- Highest efficiencies attained with 2- or 3-step process
- Sticking coefficient for Se is low → **excessive Se use**
- Volatile Ga species form with Se → **loss of Ga**

Selenization Pathways to 2SSS CuInGaSe₂ Manufacturing

Se Incorporation

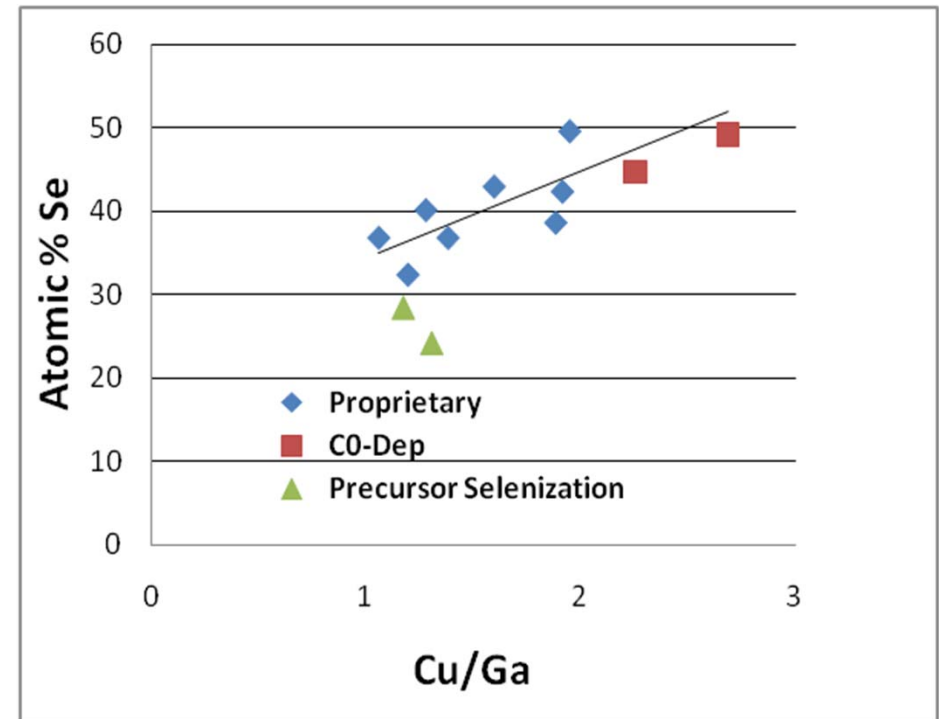
- **Se incorporation is a function of substrate temperature(Tss) and Se/metal flux**
- **Approximately 50 atomic % Se is required**
- **In the first step of a 2SSS process Cu/Ga > 1 is required and a Tss of 300 °C is used which requires a Se/metal flux of order 6 to reach 50% Se**



Selenization Pathways to 2SSS CuInGaSe_2 Manufacturing

Proprietary Process Developed

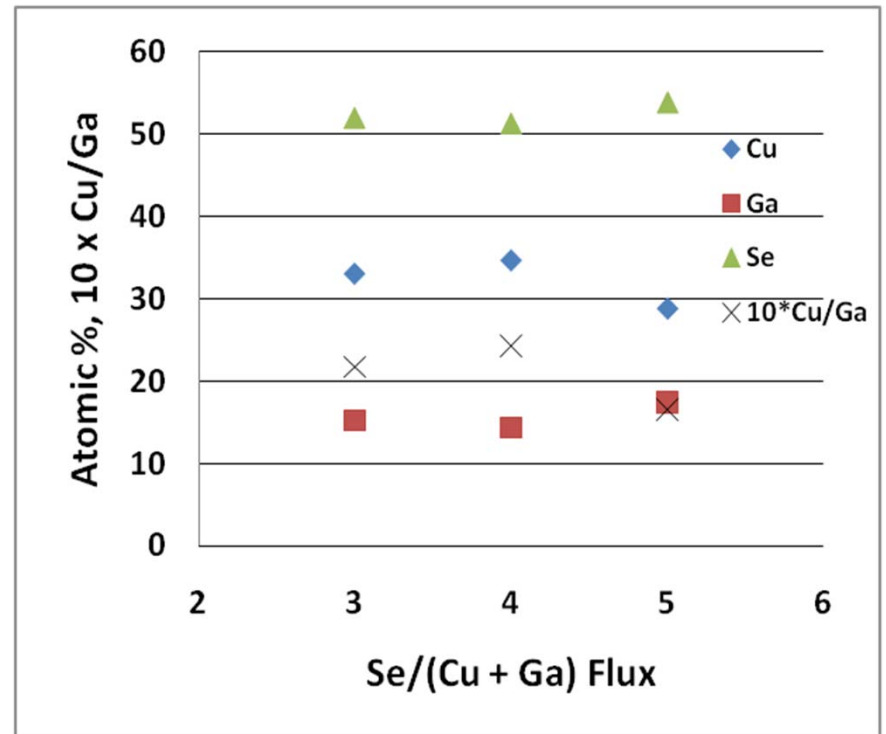
- **Co-deposition** produces highest efficiency but is most difficult to manufacture
- **Precursor Selenization** is easier to manufacture but lower efficiency
- Se and Ga have a complex incorporation interdependence which results in inefficient incorporation
- **New process** spans the range in Se and Ga utilization between the two “endpoint” processes



Selenization Pathways to 2SSS CuInGaSe_2 Manufacturing

Proprietary Process Provides Additional Control

- Additional control of the proprietary process maintains 50% Se content over a range of Cu/Ga ratios
- 50% Se can be attained at Cu/Ga of 1.7 compared to a value of 2.8 for co-deposited films indicating a significant reduction in Ga loss
- Allowing a small increase in Cu/Ga from 1.7 to 2.1 results in significant reduction in Se flux ratio from 5 to 3 while maintaining Se at 50%



Conclusions

- **A partnership with a Florida based industrial partner has been formed**
- **The main processing tool for the thin film pilot line is being built with x5 leveraging of budgeted funds**
- **The processing approach has been switched to roll-to-roll on a stainless steel web**
- **Lab scale experiments are being conducted to develop new processing pathways**
- **A proprietary process for improved control and utilization of Ga and Se has been developed**